Central™
Semiconductor Corp.

PROCESS CPD80V

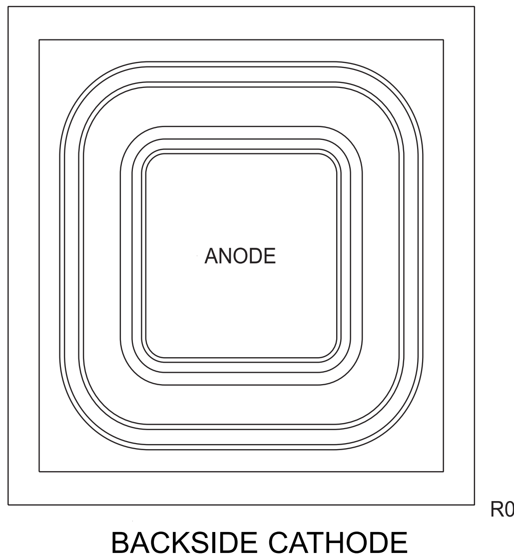
Switching Diode

High Voltage Switching Diode Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	16 x 16 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	6.5 x 6.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au.As - 13,000Å

GEOMETRY



BACKSIDE CATHODE

GROSS DIE PER 4 INCH WAFER
42,040

PRINCIPAL DEVICE TYPES
CMPD2003
CMPD2004
CMPD2005
1N3070
CMDD2004
CMSD2004
CMOD2004
CMXD2004
CMLD2004

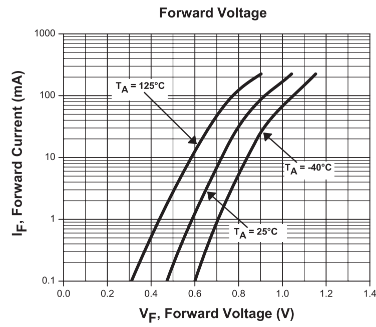
145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

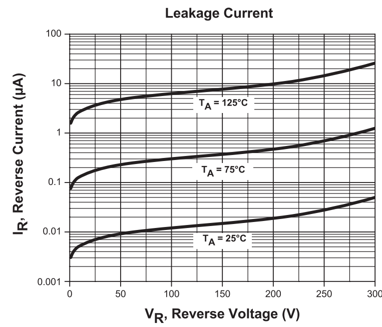
R2 (8-October 2008)

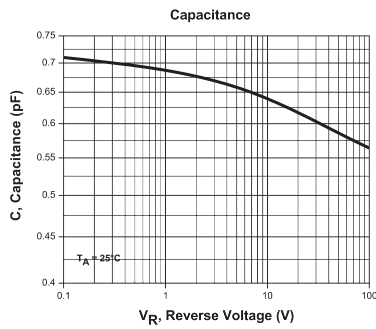
Central™ Semiconductor Corp.

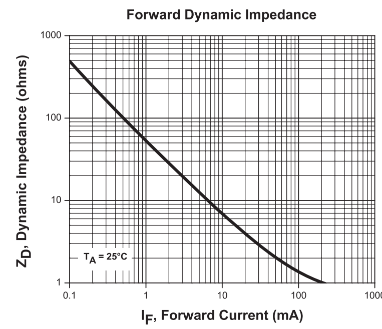
PROCESS CPD80V

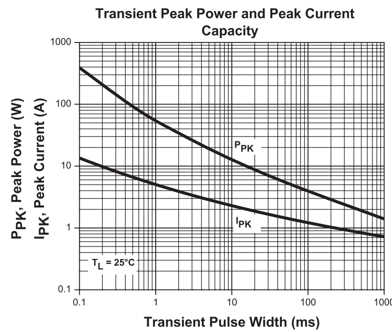
Typical Electrical Characteristics

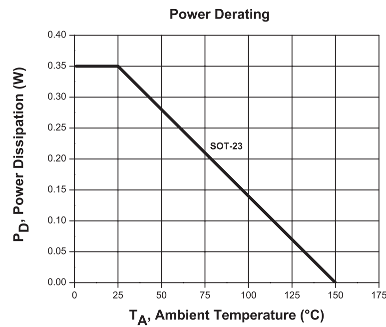












145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

R2 (8-October 2008)